

Fig.1

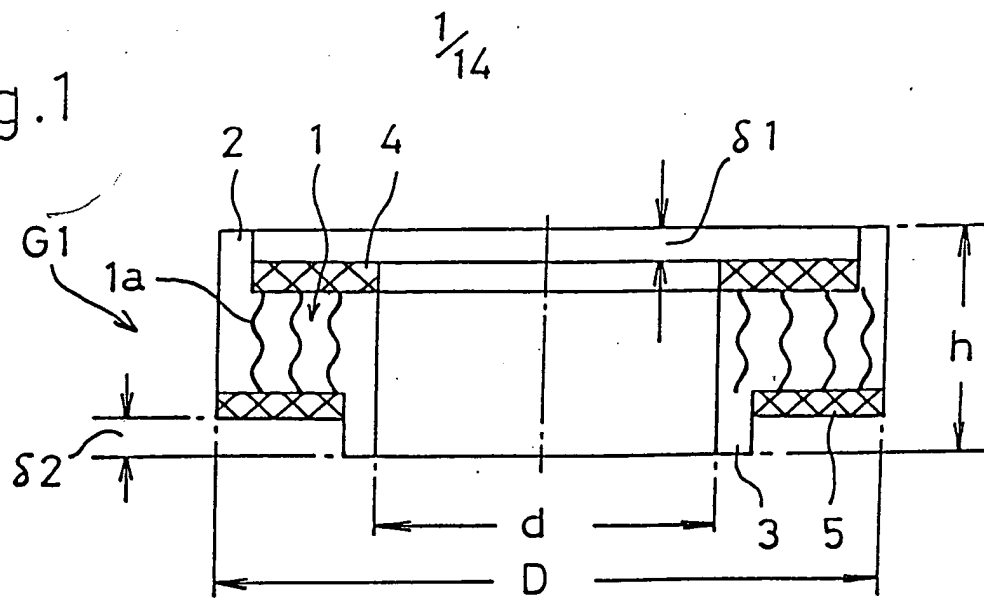


Fig.2

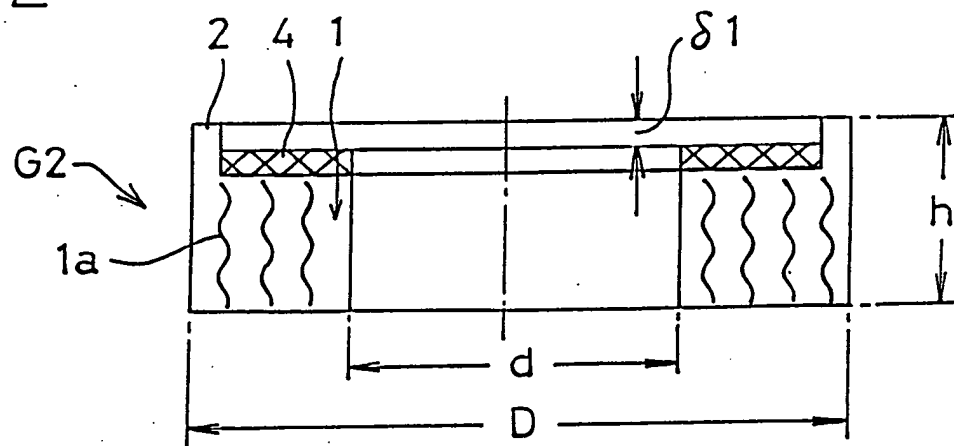


Fig.3

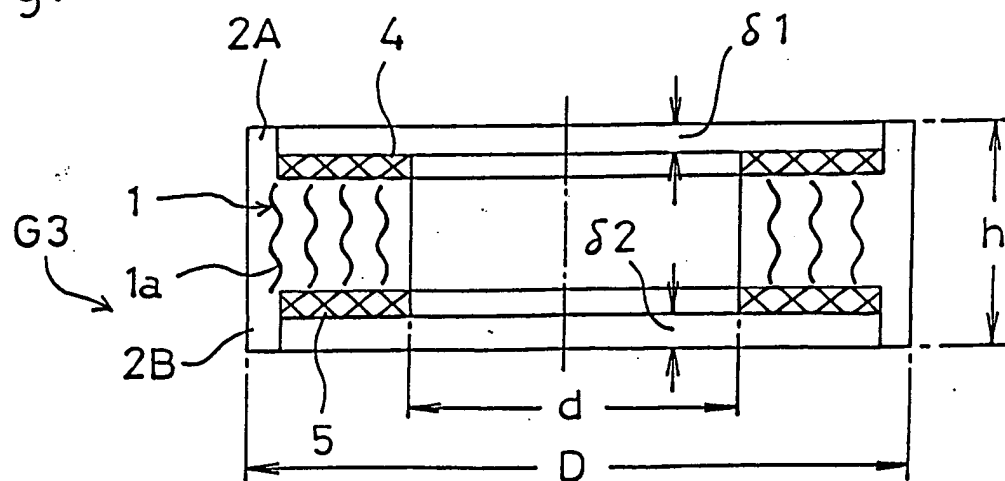


Fig.4

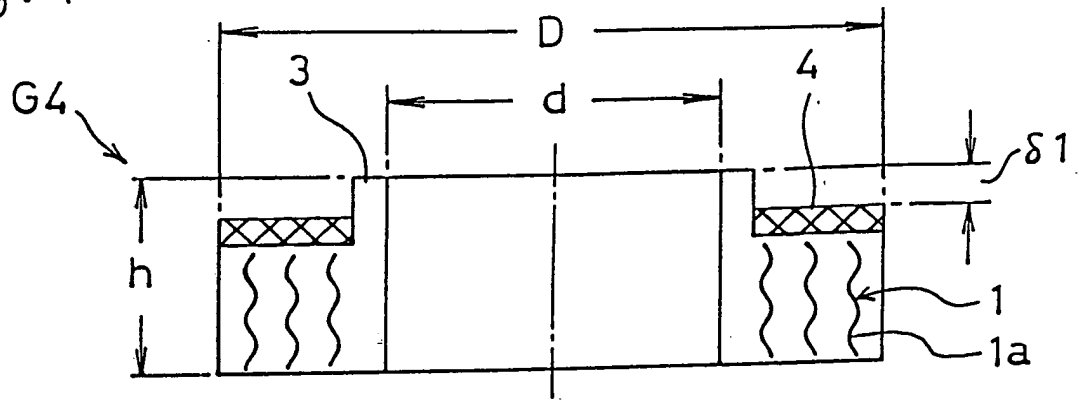


Fig.5

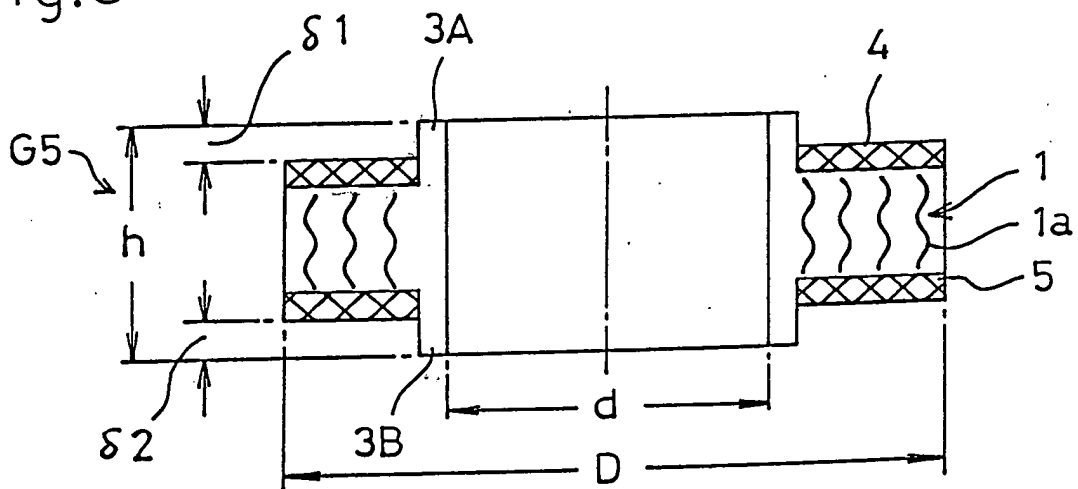


Fig.6

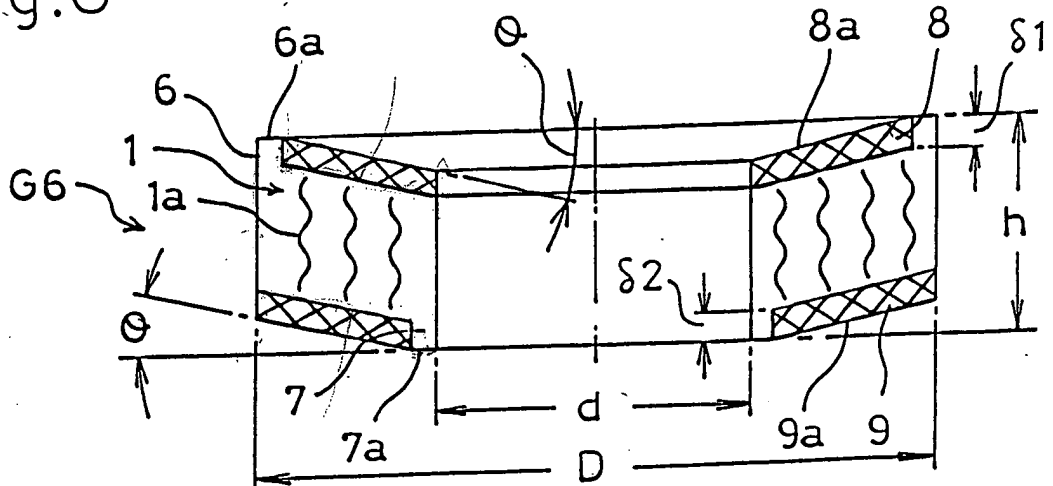


Fig.7

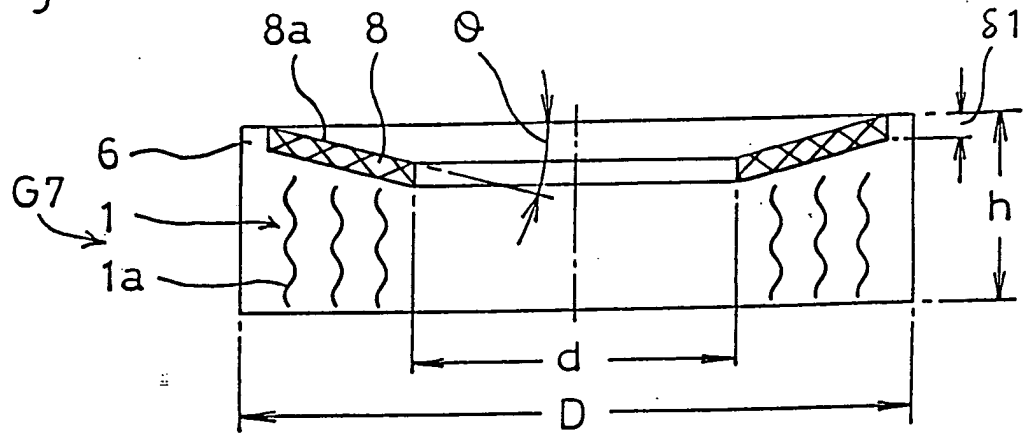


Fig.8

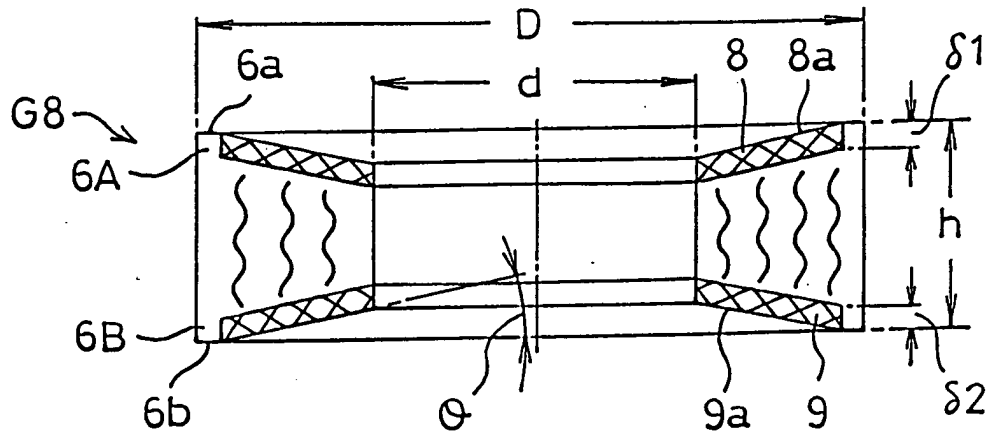
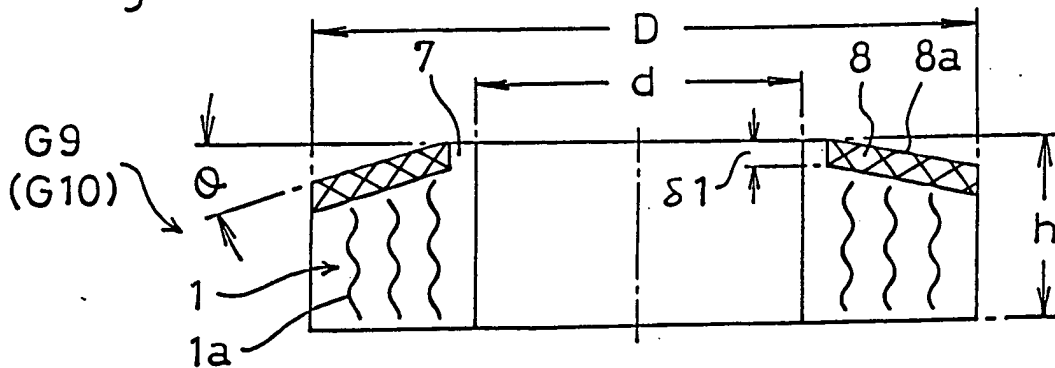


Fig.9



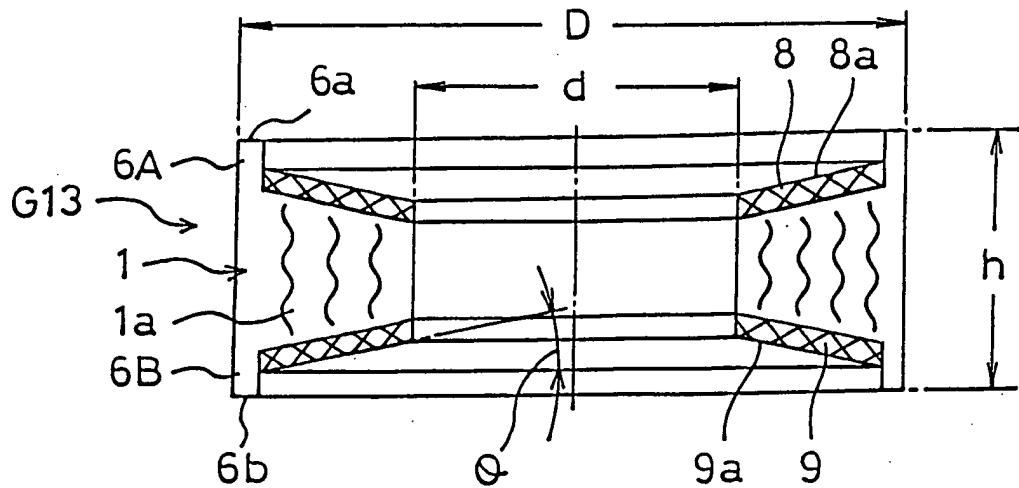


Fig.14

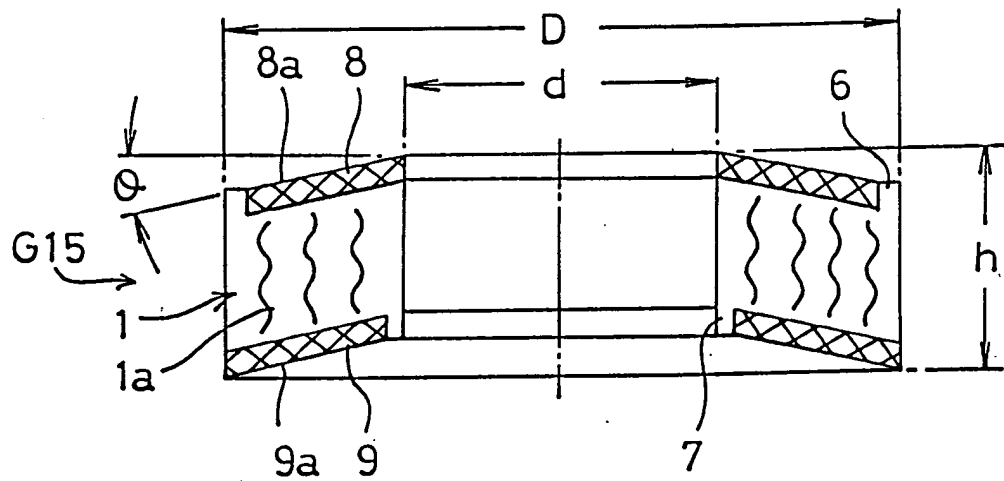


Fig.15

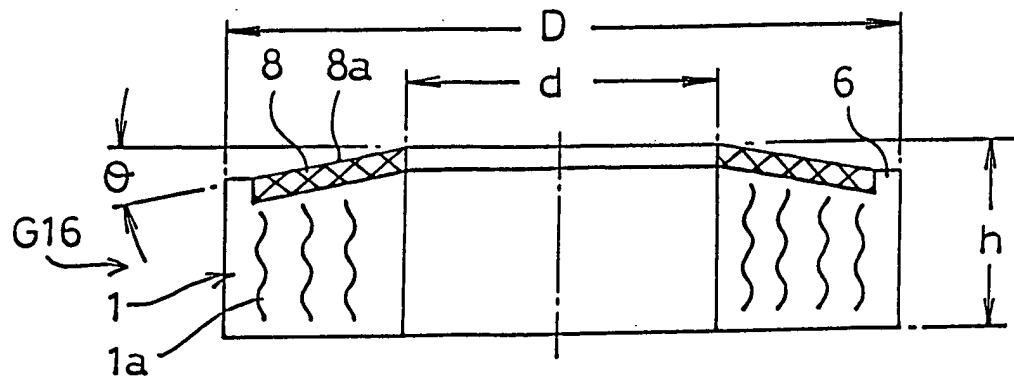


Fig.16

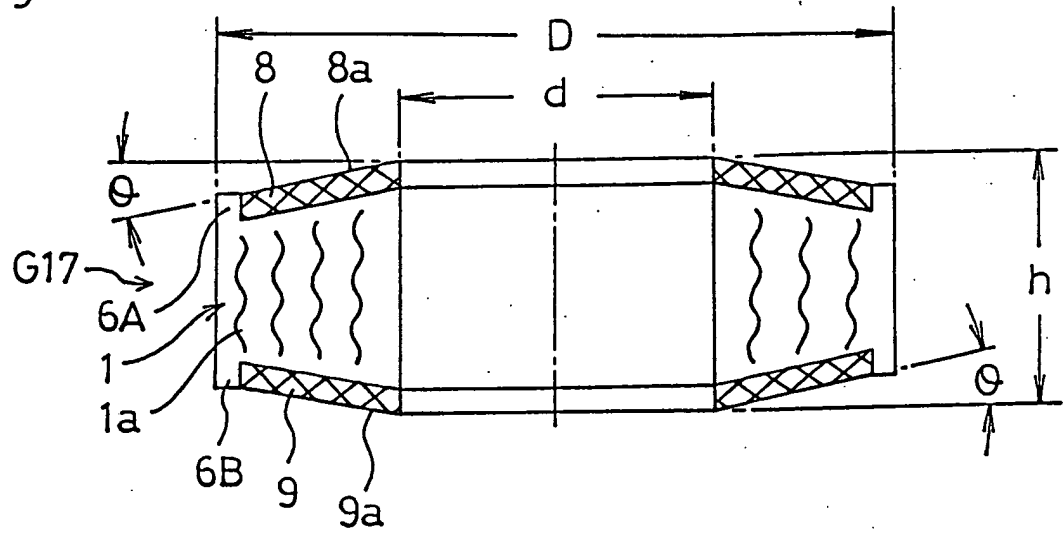


Fig.17

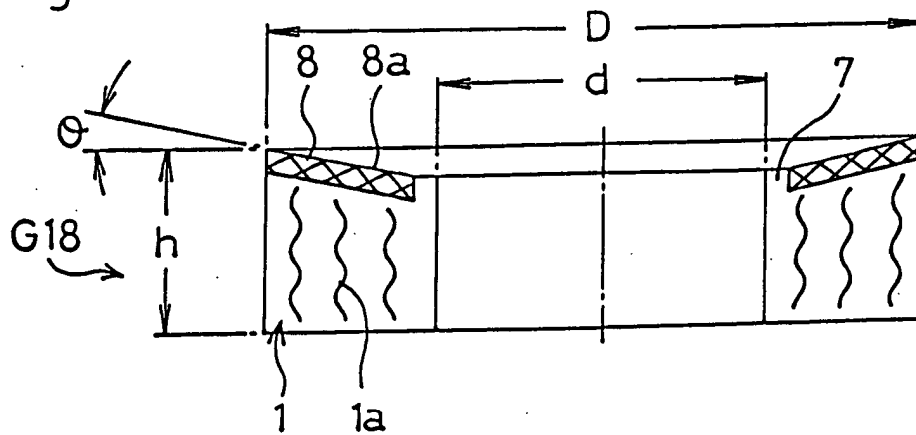


Fig.18

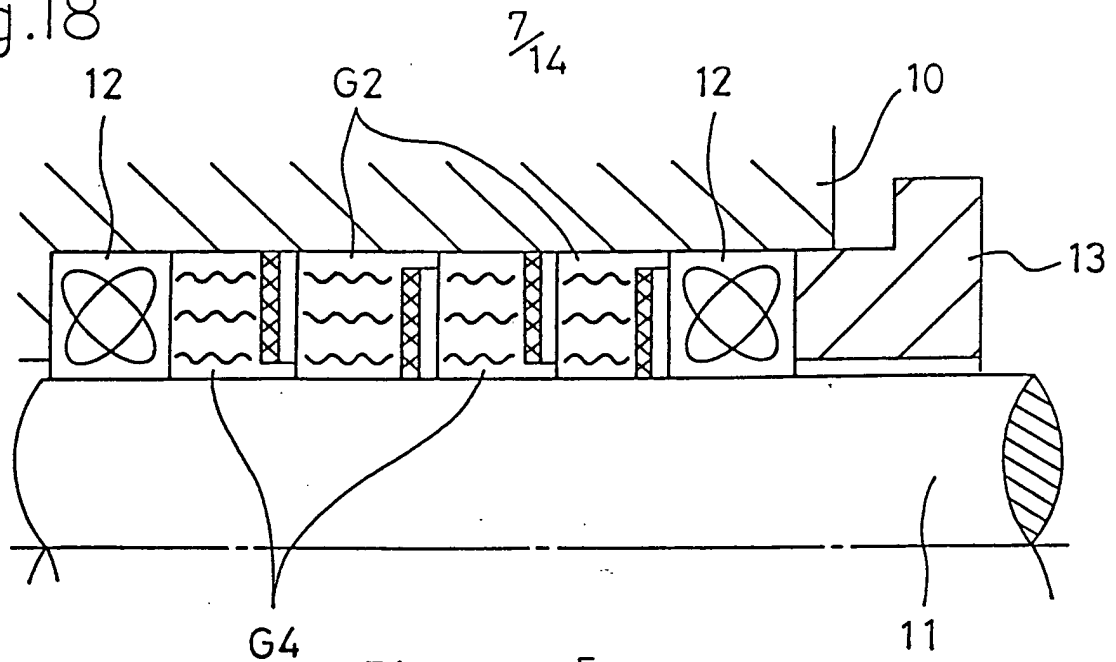


Fig.19

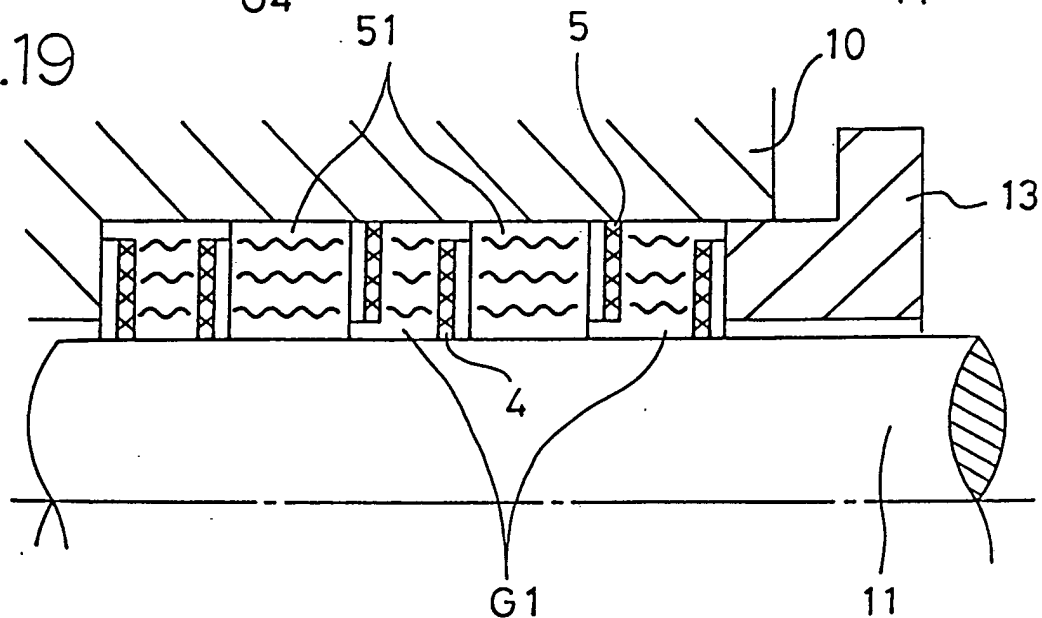
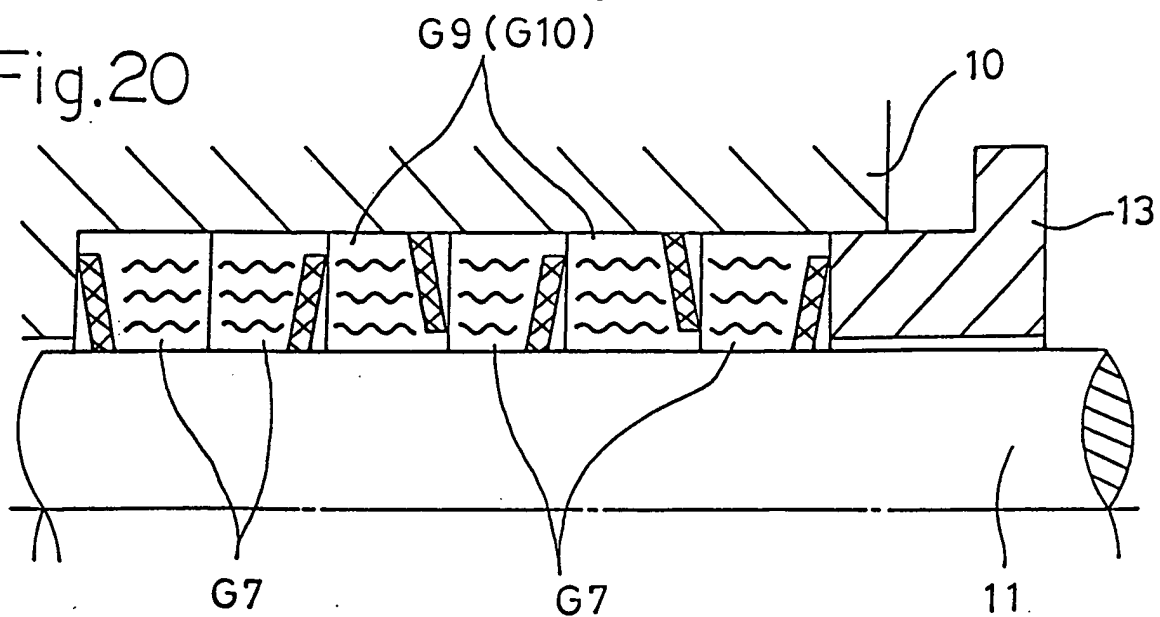


Fig.20



A cross-sectional diagram of a semiconductor device. It shows a substrate 1 with a patterned layer 2 on its surface. The patterned layer 2 contains conductive particles G2 (G4). Above the patterned layer 2 is a thin layer 4. Arrows labeled 14 indicate incident light rays passing through the structure.

A cross-sectional view of a device. It consists of a central layer 1 with a wavy internal structure. This central layer is flanked by side layers 2 and 3, which are separated from the central layer by wavy lines. The entire assembly is capped by end layers 4 and 5, which have a cross-hatched pattern. A force G1 is indicated by an arrow pointing to the left, applied to the left side of the central layer 1. A label 1a points to the left boundary of the central layer 1.



Fig. 23

KINDS		STRESS GENERATED WHEN COMPRESSED
PACKINGS OF THE INVENTION	G 1	
	G 6	
PRIOR ART PACKING	G 0 1	
COMPARISON PACKINGS	G 0 2	
	G 0 3	

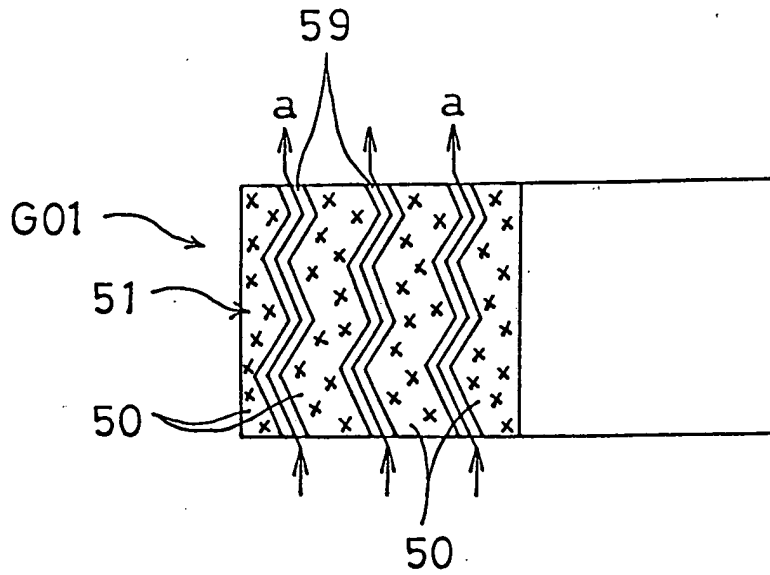
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Fig. 24

		USE EXAMPLE 1 (FIG. 18)	USE EXAMPLE 2 (FIG. 19)	USE EXAMPLE 3 (FIG. 20)	USE EXAMPLE 4 (FIG. 20)	USE EXAMPLE 5 (FIG. 20)	USE EXAMPLE 6 (FIG. 26)	USE EXAMPLE 7 (FIG. 27)	USE EXAMPLE 8 (FIG. 29)
LEAK AMOUNT	TIGHTENING FACE PRESSURE 100	0.2	0.1	1.0	0.2	0.5	90	100	60
	TIGHTENING FACE PRESSURE 200	0.05	0.008	0.01	0.05	0.03	1	3	2
	TIGHTENING FACE PRESSURE 300	0.0003	0.01	0.001	0.001	0.01	0.03	0.2	0.1

UNIT: LEAK AMOUNT = cc/min, TIGHTENING FACE PRESSURE = Kg/cm<sup>2</sup>

Fig.25 (



A cross-sectional view of a multi-layered structure 50. The structure consists of a top layer 51, a middle layer 52, and a bottom layer 53. The top layer 51 is divided into several rectangular regions. The first and last regions of the top layer 51 contain a cross-hatched pattern and are labeled 56. The intermediate regions of the top layer 51 contain a wavy pattern and are labeled 51. The middle layer 52 is a solid layer. The bottom layer 53 is a solid layer. The structure 50 is shown on a substrate 55. A cross-section of a lens or curved surface is shown on the right side of the structure 50, labeled 54. A dashed line indicates the center of the structure 50.

Fig.28

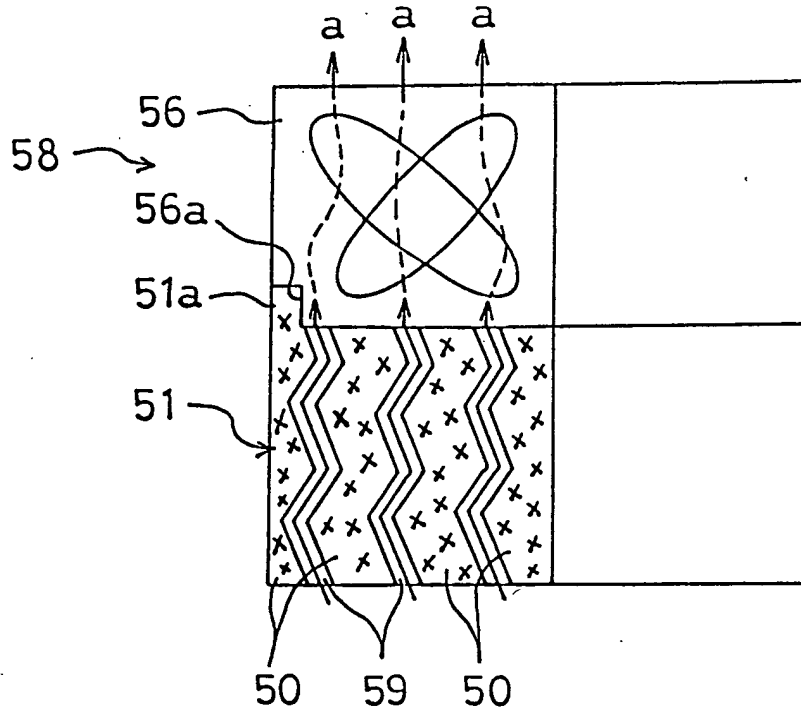
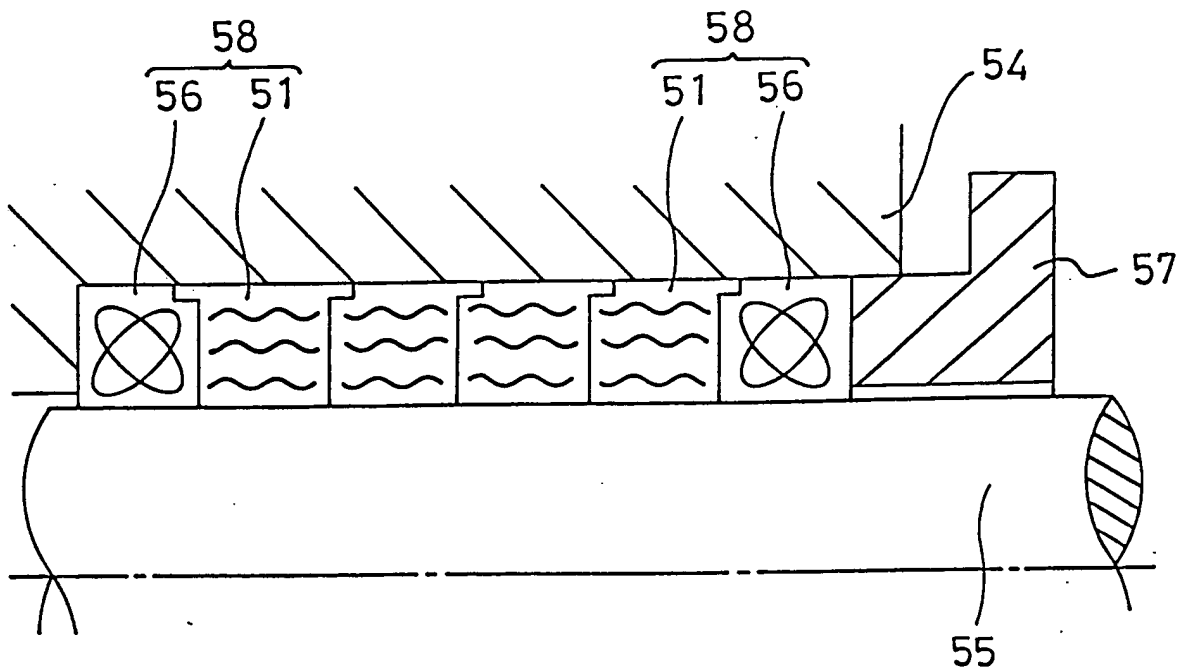


Fig.29



This diagram shows a cross-sectional view of a second embodiment of the device. It features a central core 51 with three vertical wavy lines. This core is flanked by two cross-hatched regions 60, one on the top and one on the bottom. A bracket labeled G02 spans the top and bottom cross-hatched regions. To the right of the cross-hatched regions is a rectangular block 52, which is part of a larger assembly indicated by a dashed line.

This diagram shows a cross-sectional view of a second embodiment of the device. It features a substrate 61 with a central region 51 containing three vertical wavy lines. This region is flanked by two cross-hatched areas 63. A layer 62 is positioned to the right of the central region, and an arrow G03 points towards the central region from the left.